

O P P 2 Q R S T U V W X

silicon PNP transistor in a SOT-363 Plastic Package.

$Y_{FEZ} [\quad_{CE(sat)} X C D \setminus] X$

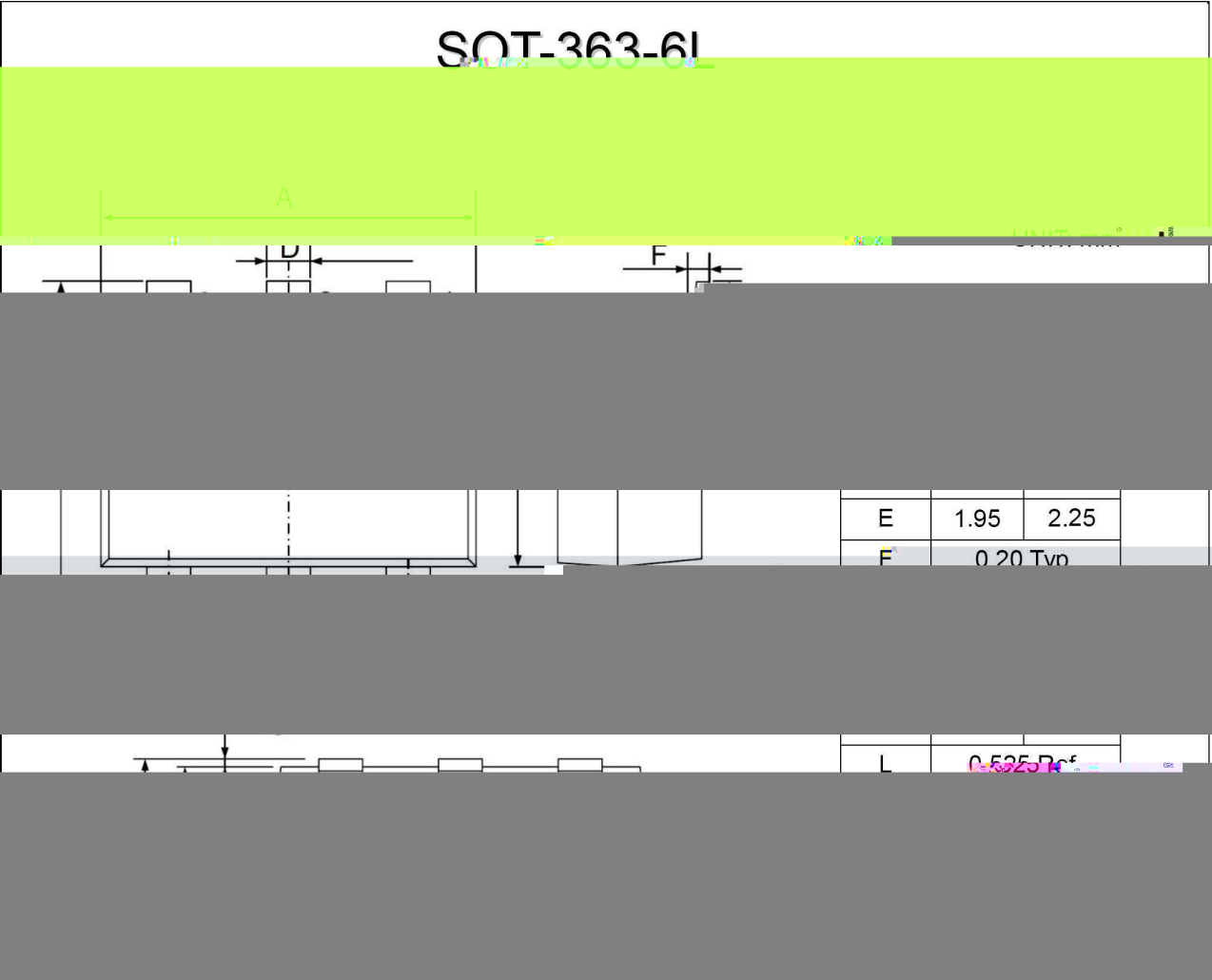
High DC Current Gain, Low Collector to Emitter Saturation Voltage. HF Product.

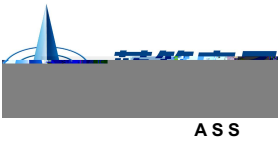
$\wedge _ \backslash a b c) d e X$

General purpose amplifier and switching.

g h Parameter	i j Symbol	h k Rating	l m Unit
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-40	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current	I_C	-200	mA

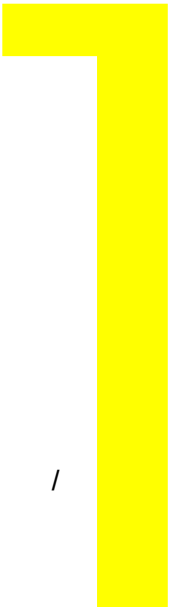
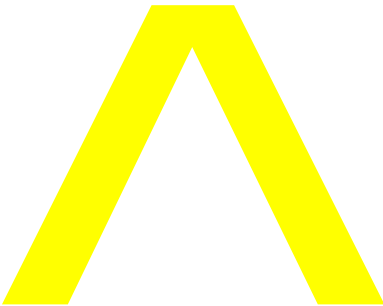
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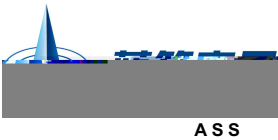




H

v w f
● f x y 1 z {
A2 f x u j | '
***: x } \ ~ j | ' Z i } \ ~ j ¢ £





H

- Note:
1.Preheating:150~180 , Time:60~90sec.
2.Peak Temp.:245±5 , Duration:5±0.5sec.
3. Cooling Speed: 2~10 /sec.
- 11501806090sec;
2245±55±0.5sec;
3210/sec.

H E / / A /

260±510±1 sec.Temp.:260±5℃Time:10±1 sec

Hs

/ REEL

Package TypeUnits 包装数量
封装形式